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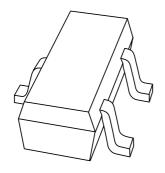
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Kind regards,

Team Nexperia

## **DISCRETE SEMICONDUCTORS**

## DATA SHEET



# BC856T; BC857T series PNP general purpose transistors

Product data sheet Supersedes data of 1999 Apr 26



## PNP general purpose transistors

BC856T; BC857T series

#### **FEATURES**

• Low current (max. 100 mA)

• Low voltage (max. 65 V).

## **APPLICATIONS**

• General purpose switching and amplification, especially in portable equipment.

## **DESCRIPTION**

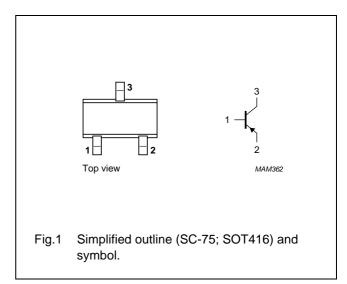
PNP transistor in an SC-75 (SOT416) plastic package. NPN complements: BC846T; BC847T series.

## **MARKING**

| TYPE NUMBER | MARKING CODE |
|-------------|--------------|
| BC856AT     | 3A           |
| BC856BT     | 3B           |
| BC857AT     | 3E           |
| BC857BT     | 3F           |
| BC857CT     | 3G           |

#### **PINNING**

| PIN | DESCRIPTION |
|-----|-------------|
| 1   | base        |
| 2   | emitter     |
| 3   | collector   |



## **LIMITING VALUES**

In accordance with the Absolute Maximum Rating System (IEC 60134).

| SYMBOL           | PARAMETER                     | CONDITIONS                       | MIN. | MAX. | UNIT |
|------------------|-------------------------------|----------------------------------|------|------|------|
| V <sub>CBO</sub> | collector-base voltage        | open emitter                     |      |      |      |
|                  | BC856AT; BC856BT              |                                  | _    | -80  | V    |
|                  | BC857AT; BC857BT; BC857CT     |                                  | _    | -50  | V    |
| V <sub>CEO</sub> | collector-emitter voltage     | open base                        |      |      |      |
|                  | BC856AT; BC856BT              |                                  | _    | -65  | V    |
|                  | BC857AT; BC857BT; BC857CT     |                                  | _    | -45  | V    |
| V <sub>EBO</sub> | emitter-base voltage          | open collector                   | _    | -5   | V    |
| I <sub>C</sub>   | collector current (DC)        |                                  | _    | -100 | mA   |
| I <sub>CM</sub>  | peak collector current        |                                  | _    | -200 | mA   |
| I <sub>BM</sub>  | peak base current             |                                  | _    | -100 | mA   |
| P <sub>tot</sub> | total power dissipation       | T <sub>amb</sub> ≤ 25 °C; note 1 | -    | 150  | mW   |
| T <sub>stg</sub> | storage temperature           |                                  | -65  | +150 | °C   |
| T <sub>j</sub>   | junction temperature          |                                  | _    | 150  | °C   |
| T <sub>amb</sub> | operating ambient temperature |                                  | -65  | +150 | °C   |

#### Note

1. Transistor mounted on an FR4 printed-circuit board.

## PNP general purpose transistors

BC856T; BC857T series

## THERMAL CHARACTERISTICS

| SYMBOL              | PARAMETER                                   | CONDITIONS          | VALUE | UNIT |
|---------------------|---|---------------------|-------|------|
| R <sub>th j-a</sub> | thermal resistance from junction to ambient | in free air; note 1 | 833   | K/W  |

#### Note

1. Transistor mounted on an FR4 printed-circuit board.

## **CHARACTERISTICS**

 $T_{amb}$  = 25 °C unless otherwise specified.

| SYMBOL             | PARAMETER  | CONDITIONS   | MIN. | TYP. | MAX. | UNIT |
|--------------------|--|--|------|------|------|------|
| I <sub>CBO</sub>   | collector-base cut-off current                               | $V_{CB} = -30 \text{ V}; I_E = 0$  | _    | _    | -15  | nA   |
|                    |  | $V_{CB} = -30 \text{ V}; I_E = 0; T_j = 150 ^{\circ}\text{C}$                  | _    | _    | -5   | μΑ   |
| I <sub>EBO</sub>   | emitter cut-off current                                      | $V_{EB} = -5 \text{ V; } I_C = 0$  | _    | _    | -100 | nA   |
| h <sub>FE</sub>    | DC current gain  | $V_{CE} = -5 \text{ V; } I_{C} = -2 \text{ mA}$                                |      |      |      |      |
|                    | BC856AT; BC857AT   |  | 125  | _    | 250  |      |
|                    | BC856BT; BC857BT   |  | 220  | _    | 475  |      |
|                    | BC857CT  |  | 420  | _    | 800  |      |
| V <sub>CEsat</sub> | collector-emitter saturation                                 | $I_C = -10 \text{ mA}; I_B = -0.5 \text{ mA}$                                  | _    | _    | -200 | mV   |
| voltage            | $I_C = -100 \text{ mA}; I_B = -5 \text{ mA}; \text{ note 1}$ | _  | _    | -400 | mV   |      |
| V <sub>BE</sub>    | base-emitter voltage   | $I_C = -2 \text{ mA}; V_{CE} = -5 \text{ V}$                                   | -580 | _    | -700 | mV   |
|                    |  | $I_C = -10 \text{ mA}; V_{CE} = -5 \text{ V}$                                  | _    | _    | -770 | mV   |
| C <sub>c</sub>     | collector capacitance  | $V_{CB} = -10 \text{ V; } f = 1 \text{ MHz; } I_E = i_e = 0$                   | _    | _    | 2.5  | pF   |
| C <sub>e</sub>     | emitter capacitance  | $V_{EB} = -0.5 \text{ V; } f = 1 \text{ MHz; } I_C = i_c = 0$                  | _    | 10   | _    | pF   |
| f <sub>T</sub>     | transition frequency   | $I_C = -10 \text{ mA}; V_{CE} = -5 \text{ V};$<br>f = 100 MHz                  | 100  | -    | -    | MHz  |
| F                  | noise figure   | $I_C = -200 \mu A; V_{CE} = -5 V;$<br>$R_S = 2 k\Omega; f = 1 kHz; B = 200 Hz$ | _    | _    | 10   | dB   |

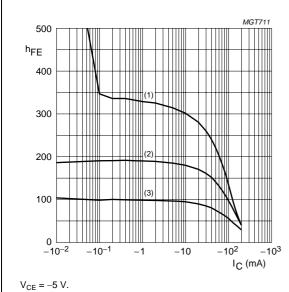
#### Note

1. Pulse test:  $t_p \le 300~\mu s;~\delta \le 0.02.$ 

## PNP general purpose transistors

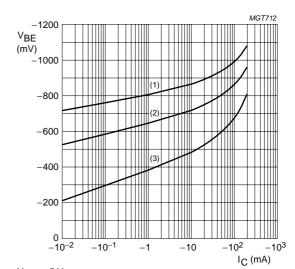
## BC856T; BC857T series

#### **GRAPHICAL INFORMATION BC857AT**



- (1)  $T_{amb} = 150 \, ^{\circ}C$ .
- (2)  $T_{amb} = 25 \, ^{\circ}C$ .
- (3)  $T_{amb} = -55 \, ^{\circ}C$ .

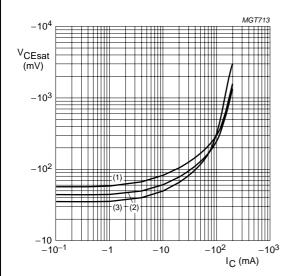
Fig.2 DC current gain; typical values.



 $V_{CE} = -5 \text{ V}.$ 

- (1)  $T_{amb} = -55 \, ^{\circ}C$
- (2)  $T_{amb} = 25 \, ^{\circ}C$ .
- (3) T<sub>amb</sub> = 150 °C.

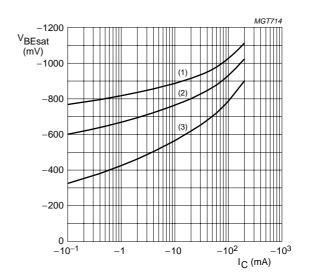
Fig.3 Base-emitter voltage as a function of collector current; typical values.



 $I_{\rm C}/I_{\rm B} = 20.$ 

- (1)  $T_{amb} = 150 \, ^{\circ}C$ .
- (2)  $T_{amb} = 25 \, ^{\circ}C$ .
- (3)  $T_{amb} = -55 \, ^{\circ}C$ .

Fig.4 Collector-emitter saturation voltage as a function of collector current; typical values.



 $I_{\rm C}/I_{\rm B} = 20$ .

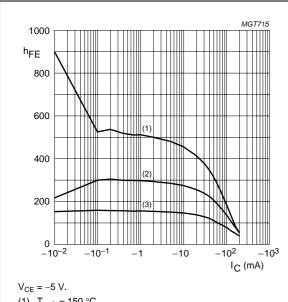
- (1)  $T_{amb} = -55 \, ^{\circ}C$ .
- (2)  $T_{amb} = 25 \, ^{\circ}C$ .
- (3)  $T_{amb} = 150 \, ^{\circ}C$ .

Fig.5 Base-emitter saturation voltage as a function of collector current; typical values.

## PNP general purpose transistors

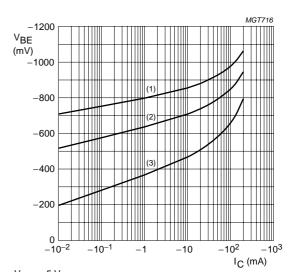
## BC856T; BC857T series

#### **GRAPHICAL INFORMATION BC857BT**



- (1)  $T_{amb} = 150 \, ^{\circ}C$ .
- (2)  $T_{amb} = 25 \, ^{\circ}C$ .
- (3)  $T_{amb} = -55 \, ^{\circ}C$ .

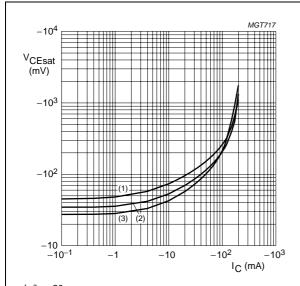
Fig.6 DC current gain; typical values.



 $V_{CE} = -5 \text{ V}.$ 

- (1)  $T_{amb} = -55 \, ^{\circ}C$
- (2)  $T_{amb} = 25 \, ^{\circ}C$ .
- (3) T<sub>amb</sub> = 150 °C.

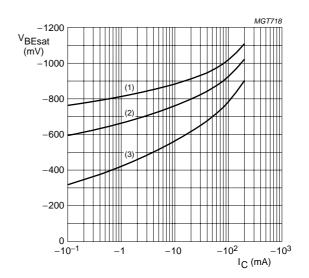
Fig.7 Base-emitter voltage as a function of collector current; typical values.



 $I_{\rm C}/I_{\rm B} = 20.$ 

- (1)  $T_{amb} = 150 \, ^{\circ}C$ .
- (2)  $T_{amb} = 25 \, ^{\circ}C$ .
- (3)  $T_{amb} = -55 \, ^{\circ}C$ .

Collector-emitter saturation voltage as a function of collector current; typical values.



 $I_{\rm C}/I_{\rm B} = 20$ .

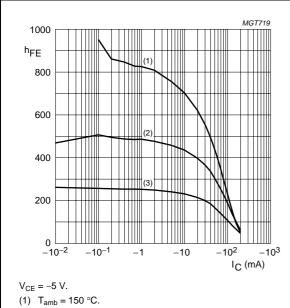
- (1)  $T_{amb} = -55 \, ^{\circ}C$ .
- (2)  $T_{amb} = 25 \, ^{\circ}C$ .
- (3)  $T_{amb} = 150 \, ^{\circ}C$ .

Fig.9 Base-emitter saturation voltage as a function of collector current; typical values.

## PNP general purpose transistors

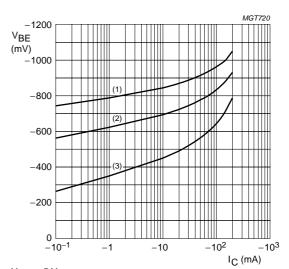
## BC856T; BC857T series

#### **GRAPHICAL INFORMATION BC857CT**



- (2)  $T_{amb} = 25 \, ^{\circ}C$ .
- (3)  $T_{amb} = -55 \, ^{\circ}C$ .

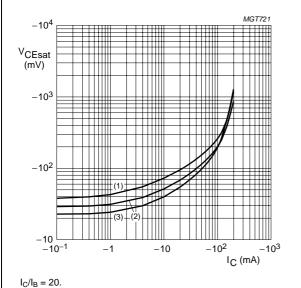
Fig.10 DC current gain; typical values.



 $V_{CE} = -5 \text{ V}.$ 

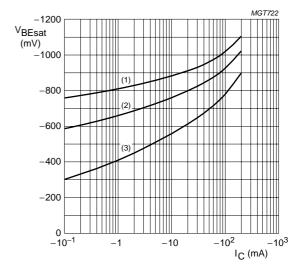
- (1)  $T_{amb} = -55 \, ^{\circ}C$
- (2) T<sub>amb</sub> = 25 °C.
- (3) T<sub>amb</sub> = 150 °C.

Fig.11 Base-emitter voltage as a function of collector current; typical values.



- (1)  $T_{amb} = 150 \, ^{\circ}C$ .
- (2)  $T_{amb} = 25 \, ^{\circ}C$ .
- (3)  $T_{amb} = -55 \, ^{\circ}C$ .

Fig.12 Collector-emitter saturation voltage as a function of collector current; typical values.



 $I_{\rm C}/I_{\rm B} = 20$ .

- (1)  $T_{amb} = -55 \, ^{\circ}C$ .
- (2)  $T_{amb} = 25 \, ^{\circ}C$ .
- (3)  $T_{amb} = 150 \, ^{\circ}C$ .

Fig.13 Base-emitter saturation voltage as a function of collector current; typical values.

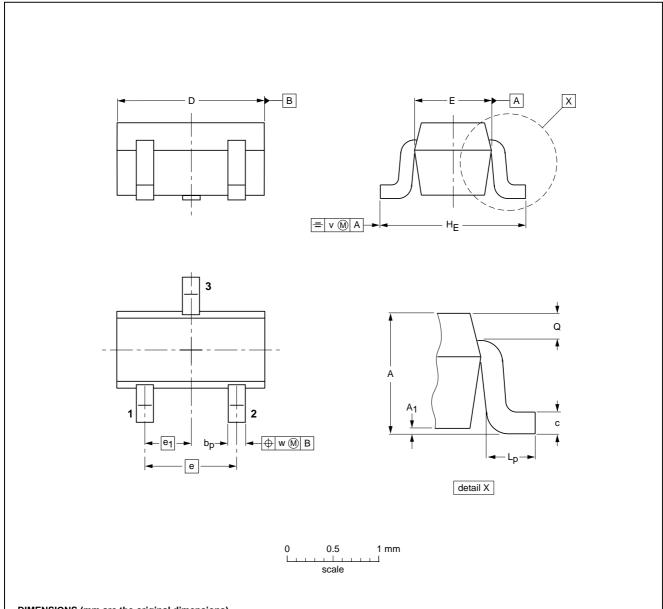
## PNP general purpose transistors

## BC856T; BC857T series

## **PACKAGE OUTLINE**

Plastic surface mounted package; 3 leads

**SOT416** 



## **DIMENSIONS** (mm are the original dimensions)

| UNIT | A            | A <sub>1</sub><br>max | bp           | С            | D          | Е          | e | e <sub>1</sub> | HE           | Lp           | Q            | v   | w   |
|------|--------------|-----------------------|--------------|--------------|------------|------------|---|----------------|--------------|--------------|--------------|-----|-----|
| mm   | 0.95<br>0.60 | 0.1                   | 0.30<br>0.15 | 0.25<br>0.10 | 1.8<br>1.4 | 0.9<br>0.7 | 1 | 0.5            | 1.75<br>1.45 | 0.45<br>0.15 | 0.23<br>0.13 | 0.2 | 0.2 |

| OUTLINE |     | REFER | EUROPEAN | ISSUE DATE |            |            |
|---------|-----|-------|----------|------------|------------|------------|
| VERSION | IEC | JEDEC | EIAJ     |            | PROJECTION | ISSUE DATE |
| SOT416  |     |       | SC-75    |            |            | 97-02-28   |

## PNP general purpose transistors

BC856T; BC857T series

#### **DATA SHEET STATUS**

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|-----------------------------------|----------------------------------|---|
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